



STGB7NC60HD, STGF7NC60HD, STGP7NC60HD

N-channel 14 A, 600 V, very fast IGBT with Ultrafast diode

Datasheet — production data

Features

- Low on-voltage drop ($V_{CE(sat)}$)
- Off losses include tail current
- Losses include diode recovery energy
- High frequency operation up to 70 kHz
- Very soft ultra fast recovery anti parallel diode

Applications

- High frequency inverters
- SMPS and PFC in both hard switch and resonant topologies
- Motor drivers

Description

These devices are very fast IGBT developed using advanced PowerMESH™ technology. This process guarantees an excellent trade-off between switching performance and low on-state behavior. These devices are well-suited for resonant or soft-switching applications.

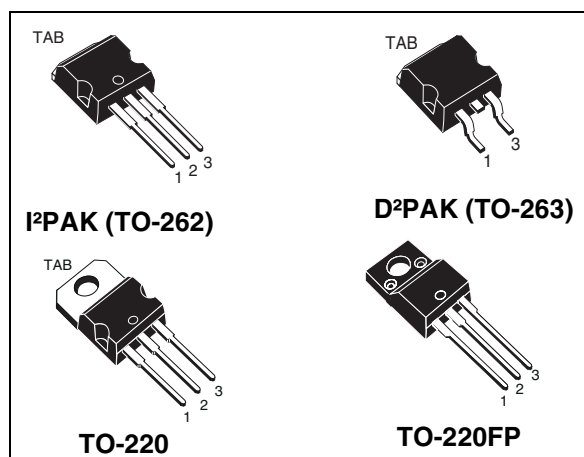


Figure 1. Internal schematic diagram

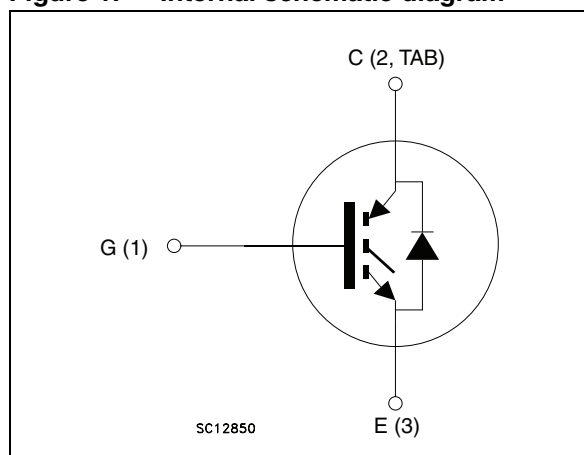


Table 1. Device summary

Order codes	Markings	Packages	Packaging
STGB7NC60HD-1	GB7NC60HD	I²PAK (TO-262)	Tube
STGB7NC60HDT4		D²PAK (TO-263)	Tape and reel
STGF7NC60HD	GF7NC60HD	TO-220FP	Tube
STGP7NC60HD	GP7NC60HD	TO-220	Tube

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
2.1	Electrical characteristics (curves)	6
2.2	Operating frequency	9
3	Test circuits	10
4	Package mechanical data	11
5	Packaging mechanical data	19
6	Revision history	21

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		I ² PAK, D ² PAK, TO-220	TO-220FP	
V _{CES}	Collector-emitter voltage (V _{GS} = 0)	600		V
V _{ECR}	Emitter-collector voltage	20		V
V _{GE}	Gate-emitter voltage	±20		V
I _C	Collector current (continuous) at T _C = 25 °C ⁽¹⁾	25	10	A
I _C	Collector current (continuous) at T _C = 100 °C ⁽¹⁾	14	6	A
I _{CM} ⁽²⁾	Collector current (pulsed)	50		A
I _F	Diode RMS forward current at T _C = 25°C	20		A
P _{TOT}	Total dissipation at T _C = 25°C	80	25	W
	Derating factor	0.64	0.20	W/°C
V _{ISO}	Insulation withstand voltage A.C. (t = 1 sec; T _C = 25°C)	--	2500	V
T _{stg}	Storage temperature	– 55 to 150		°C
T _j	Operating junction temperature			

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(max)} - T_C}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_C(T_C))}$$

2. Pulse width limited by maximum junction temperature and turn-off within RBSOA.

Table 3. Thermal data

Symbol	Parameter	Value		Unit
		I ² PAK, D ² PAK, TO-220	TO-220FP	
R _{thJC}	Thermal resistance junction-case	1.56	5.0	°C/W
R _{thJA}	Thermal resistance junction-ambient	62.5		°C/W

2 Electrical characteristics

$T_{CASE} = 25^{\circ}\text{C}$ unless otherwise specified.

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$I_C = 1\text{ mA}$, $V_{GE} = 0$	600			V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = 600\text{ V}$ $V_{CE} = 600\text{ V}$, $T_C = 125^{\circ}\text{C}$			10 1	μA mA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{ V}$			± 100	nA
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 250\text{ }\mu\text{A}$	3.75		5.75	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 7\text{ A}$ $V_{GE} = 15\text{ V}$, $I_C = 7\text{ A}$, $T_C = 125^{\circ}\text{C}$		1.85 1.7	2.5	V V

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{CE} = 15\text{ V}$, $I_C = 7\text{ A}$		4.30		S
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0$		720		pF
C_{oes}	Output capacitance			81		pF
C_{res}	Reverse transfer capacitance			17		pF
Q_g	Total gate charge	$V_{CE} = 390\text{ V}$, $I_C = 7\text{ A}$, $V_{GE} = 15\text{ V}$		35	48	nC
Q_{ge}	Gate-emitter charge			7		nC
Q_{gc}	Gate-collector charge			16		nC
I_{CL}	Turn-off SOA minimum current	$V_{clamp} = 480\text{ V}$, $T_j = 150^{\circ}\text{C}$ $R_G = 10\text{ }\Omega$, $V_{GE} = 15\text{ V}$	50			A

1. Pulsed: Pulse duration= 300 μs , duty cycle 1.5%

Table 6. Switching on

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 390\text{ V}$, $I_C = 7\text{ A}$ $R_G = 10\text{ }\Omega$, $V_{GE} = 15\text{ V}$ (see Figure 21)		18.5		ns
t_r	Current rise time			8.5		ns
$(di/dt)_{on}$	Turn-on current slope			1060		A/ μs
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 390\text{ V}$, $I_C = 7\text{ A}$ $R_G = 10\text{ }\Omega$, $V_{GE} = 15\text{ V}$, $T_j = 125^{\circ}\text{C}$ (see Figure 21)	-	18.5	-	ns
t_r	Current rise time			7		ns
$(di/dt)_{on}$	Turn-on current slope			1000		A/ μs

Table 7. Switching off

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _r (V _{off})	Off voltage rise time	V _{CC} = 390 V, I _C = 7 A, R _G = 10 Ω , V _{GE} = 15 V	-	27	-	ns
t _d (off)	Turn-off delay time			72		ns
t _f	Current fall time			60		ns
t _r (V _{off})	Off voltage rise time	V _{CC} = 390 V, I _C = 7 A, R _G = 10 Ω , V _{GE} = 15 V T _j = 125 °C		56		ns
t _d (off)	Turn-off delay time			116		ns
t _f	Current fall time			105		ns

Table 8. Switching energy

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
Eon ⁽¹⁾	Turn-on switching losses	V _{CC} = 390 V, I _C = 7 A R _G = 10 Ω, V _{GE} = 15 V,	-	95	125	μJ
E _{off} ⁽²⁾	Turn-off switching loss			115	150	μJ
E _{ts}	Total switching loss			210	275	μJ
Eon ⁽¹⁾	Turn-on switching losses	V _{CC} = 390 V, I _C = 7 A R _G = 10 Ω, V _{GE} = 15 V, T _j = 125°C		140		μJ
E _{off} ⁽²⁾	Turn-off switching loss			215		μJ
E _{ts}	Total switching loss			355		μJ

1. E_{on} is the turn-on losses when a typical diode is used in the test circuit. If the IGBT is offered in a package with a co-pack diode, the co-pack diode is used as external diode. IGBTs and diode are at the same temperature ($25\text{ }^\circ\text{C}$ and $125\text{ }^\circ\text{C}$).

2. Turn-off losses include also the tail of the collector current.

Table 9. Collector-emitter diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _f	Forward on-voltage	If = 3.5 A If = 3.5 A, T _J = 125 °C	-	1.3 1.1	1.9	V V
t _{rr} t _a Q _{rr} I _{rrm} S	Reverse recovery time Reverse recovery charge Reverse recovery current Softness factor of the diode	If = 7 A, V _R = 40 V, di/dt = 100 A/μs		37 22 40 2.1 0.68		ns ns nC A
t _{rr} t _a Q _{rr} I _{rrm} S	Reverse recovery time Reverse recovery charge Reverse recovery current Softness factor of the diode	If = 7 A, V _R = 40 V, T _J = 125 °C, di/dt = 100 A/μs		61 34 98 3.2 0.79		ns ns nC A

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

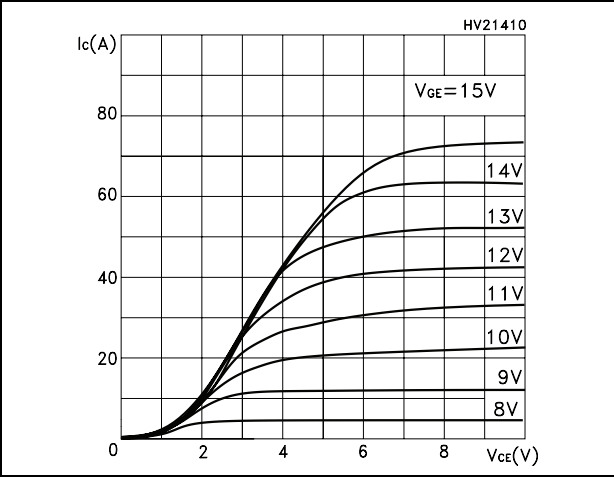


Figure 3. Transfer characteristics

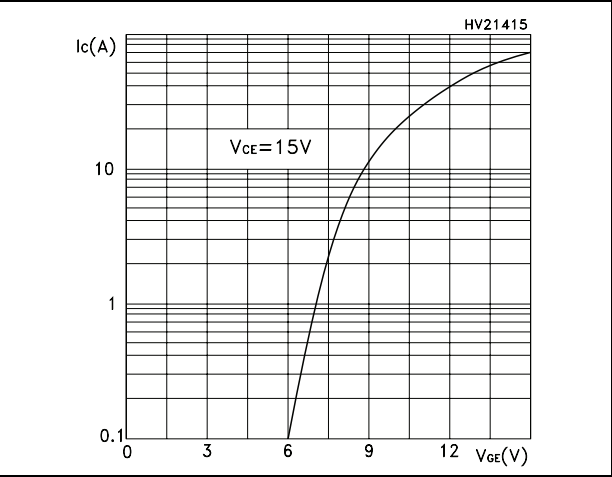


Figure 4. Transconductance

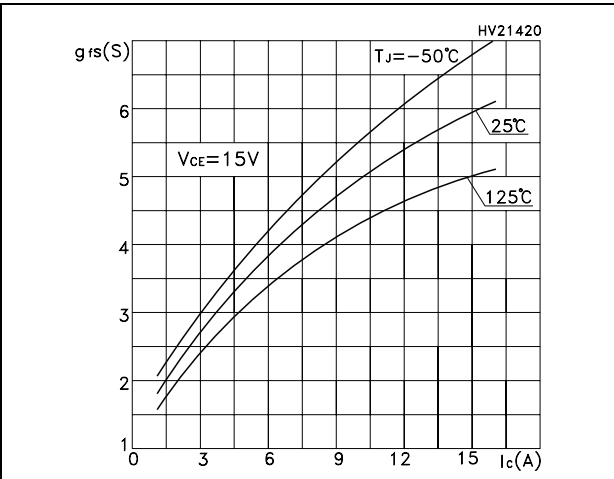


Figure 5. Collector-emitter on voltage vs. temperature

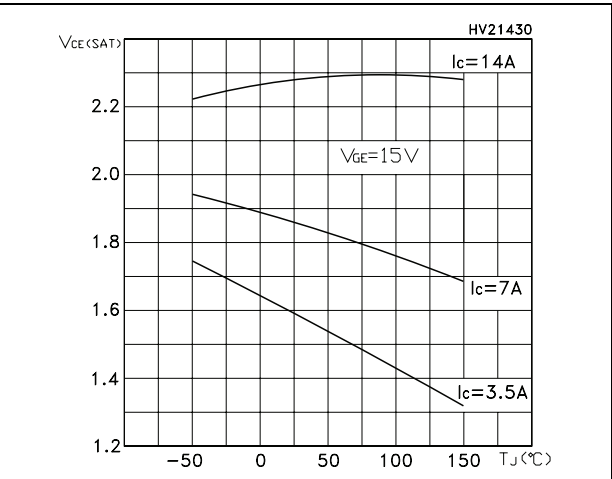


Figure 6. Collector-emitter on voltage vs. collector current

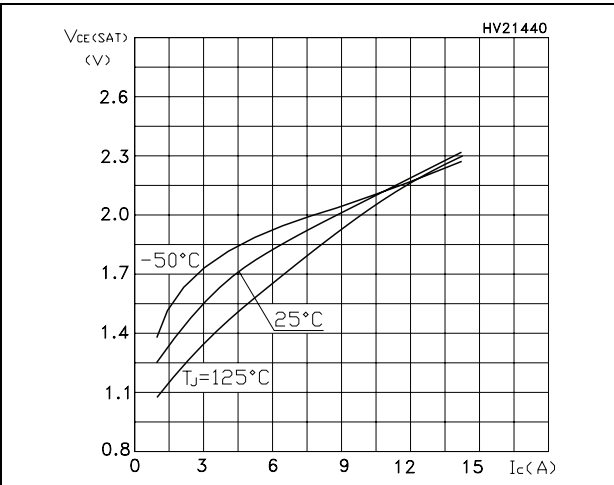


Figure 7. Normalized gate threshold vs. temperature

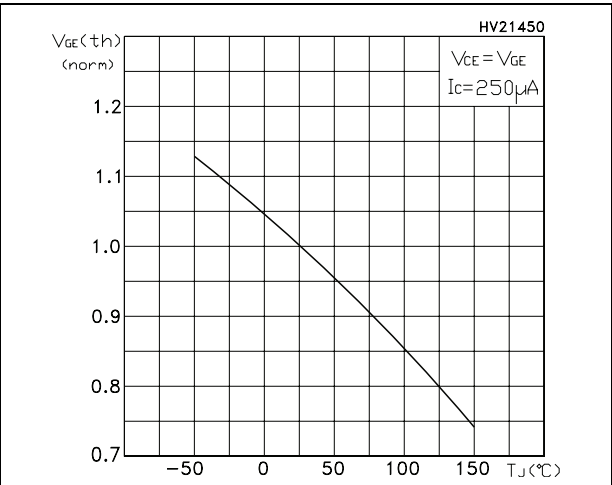


Figure 8. Normalized breakdown voltage vs temperature

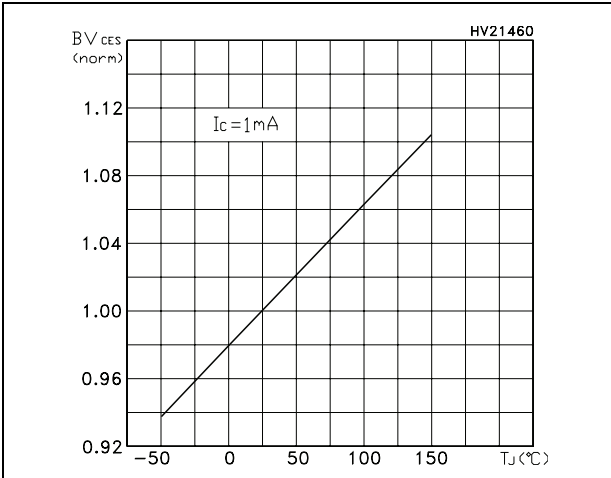


Figure 9. Gate charge vs. gate-emitter voltage

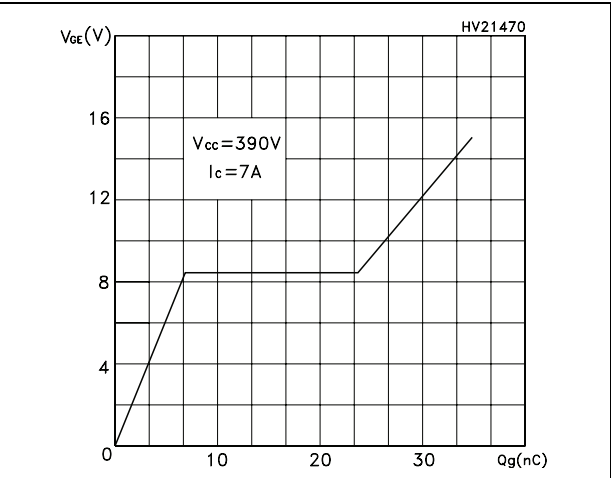


Figure 10. Capacitance variations

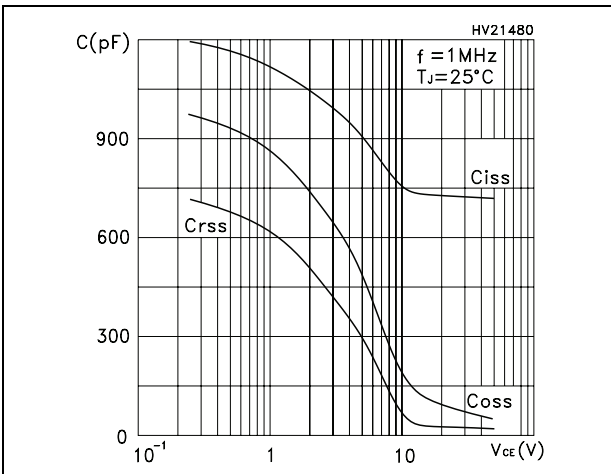


Figure 11. Total switching losses vs. temperature

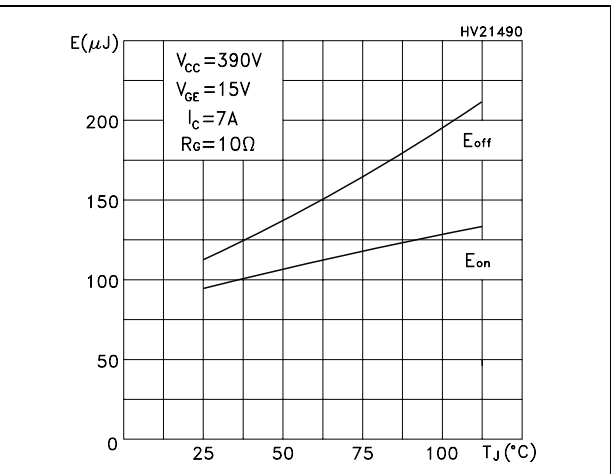


Figure 12. Total switching losses vs. gate resistance

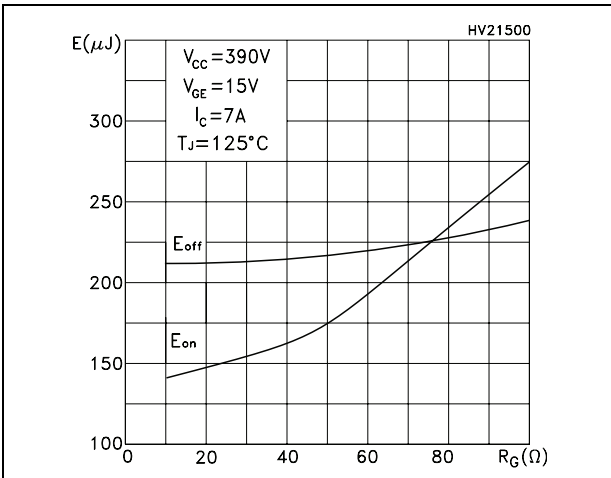


Figure 13. Total switching losses vs collector current

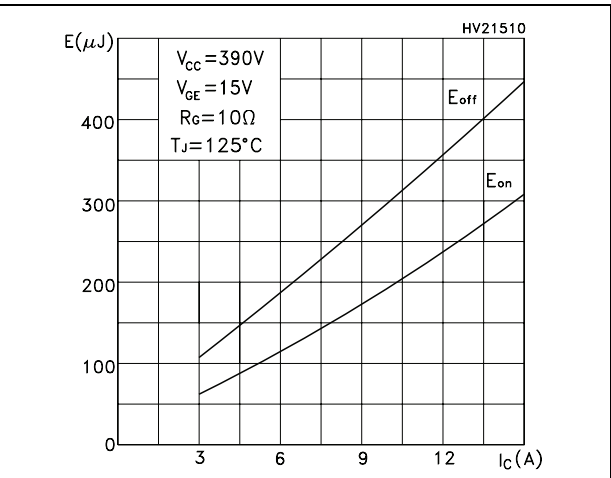


Figure 14. Emitter-collector diode characteristics

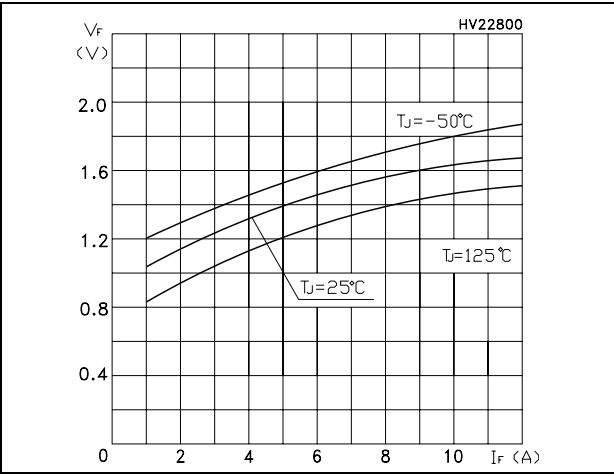


Figure 15. Turn-off SOA

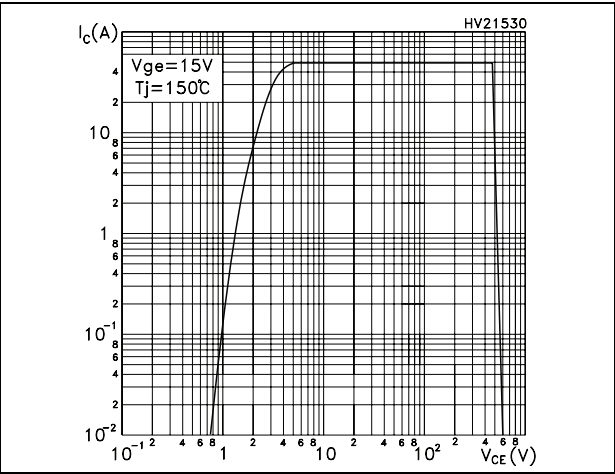


Figure 16. Thermal impedance for I²PAK, D²PAK and TO-220

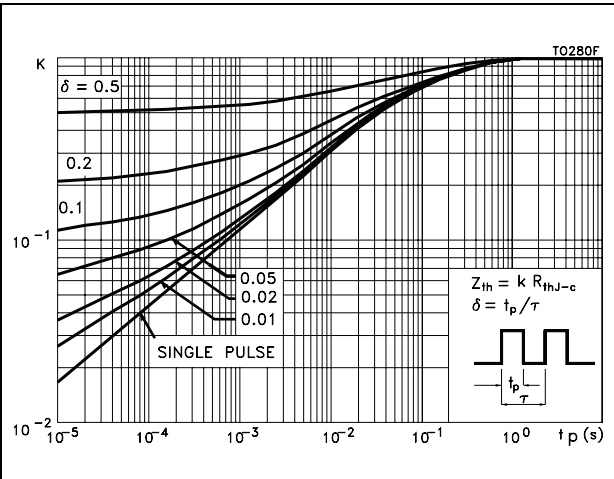
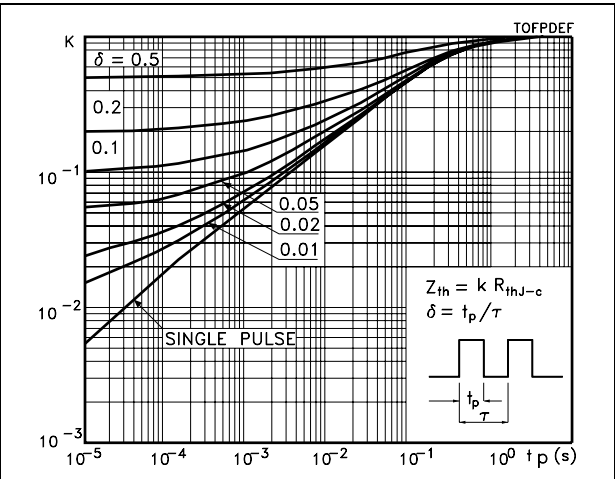
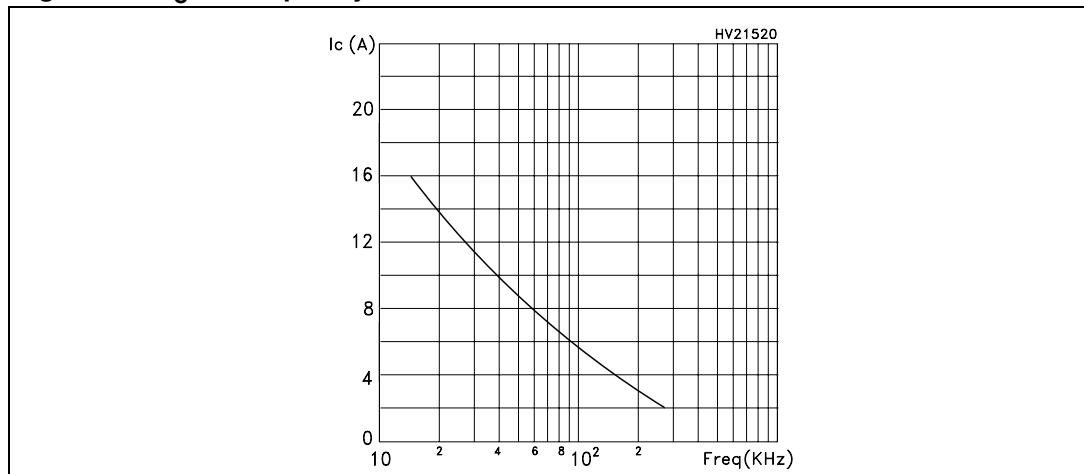


Figure 17. Thermal impedance for TO-220FP



2.2 Operating frequency

Figure 18. I_C vs. frequency



For a fast IGBT suitable for high frequency applications, the typical collector current vs. maximum operating frequency curve is reported. That frequency is defined as follows:

Equation 1

$$f_{MAX} = (P_D - P_C) / (E_{ON} + E_{OFF})$$

The maximum power dissipation is limited by maximum junction to case thermal resistance:

Equation 2

$$P_D = \Delta T / R_{THJ-C}$$

considering $\Delta T = T_J - T_C = 125^\circ\text{C} - 75^\circ\text{C} = 50^\circ\text{C}$

The conduction losses are:

Equation 3

$$P_C = I_C * V_{CE(SAT)} * \delta$$

with 50% of duty cycle, $V_{CE(sat)}$ typical value $T_C = 125^\circ\text{C}$.

Power dissipation during ON & OFF commutations is due to the switching frequency:

Equation 4

$$P_{SW} = (E_{ON} + E_{OFF}) * \text{freq.}$$

Typical values $T_C = 125^\circ\text{C}$ for switching losses are used (test conditions: $V_{CE} = 390\text{ V}$, $V_{GE} = 15\text{ V}$, $R_G = 3.3\ \Omega$). Furthermore, diode recovery energy is included in the E_{ON} , while the tail of the collector current is included in the E_{OFF} measurements.

3 Test circuits

Figure 19. Test circuit for inductive load switching

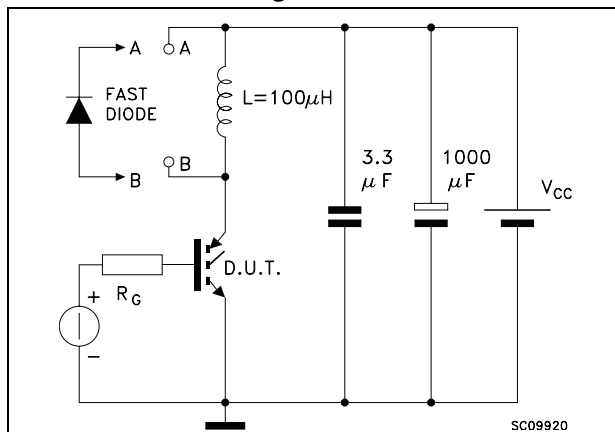


Figure 20. Gate charge test circuit

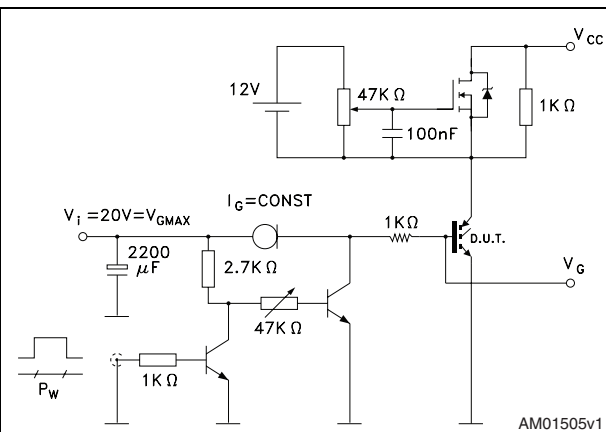


Figure 21. Switching waveform

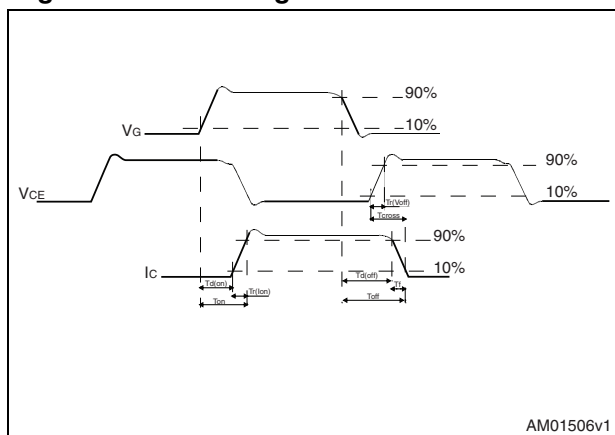
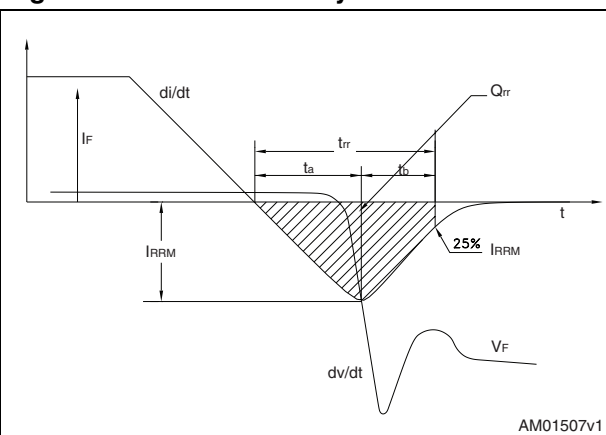


Figure 22. Diode recovery time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 10. I²PAK (TO-262) mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.40		4.60
A1	2.40		2.72
b	0.61		0.88
b1	1.14		1.70
c	0.49		0.70
c2	1.23		1.32
D	8.95		9.35
e	2.40		2.70
e1	4.95		5.15
E	10		10.40
L	13		14
L1	3.50		3.93
L2	1.27		1.40

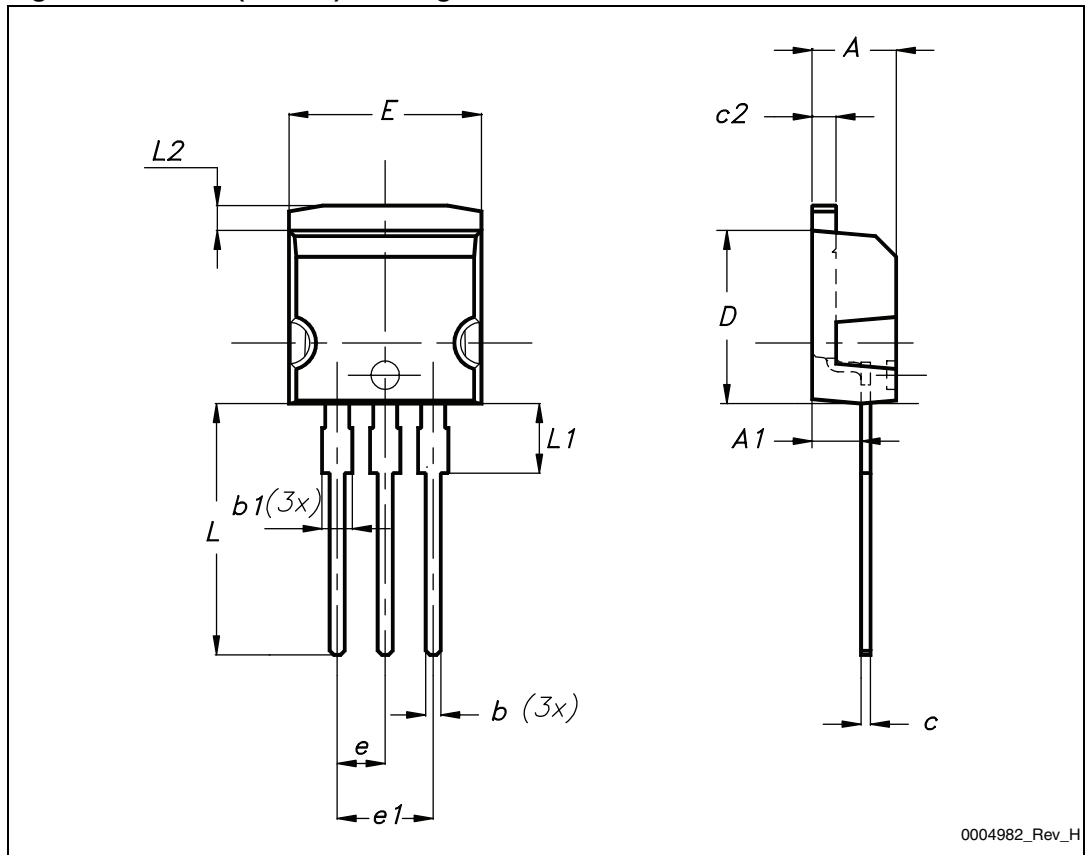
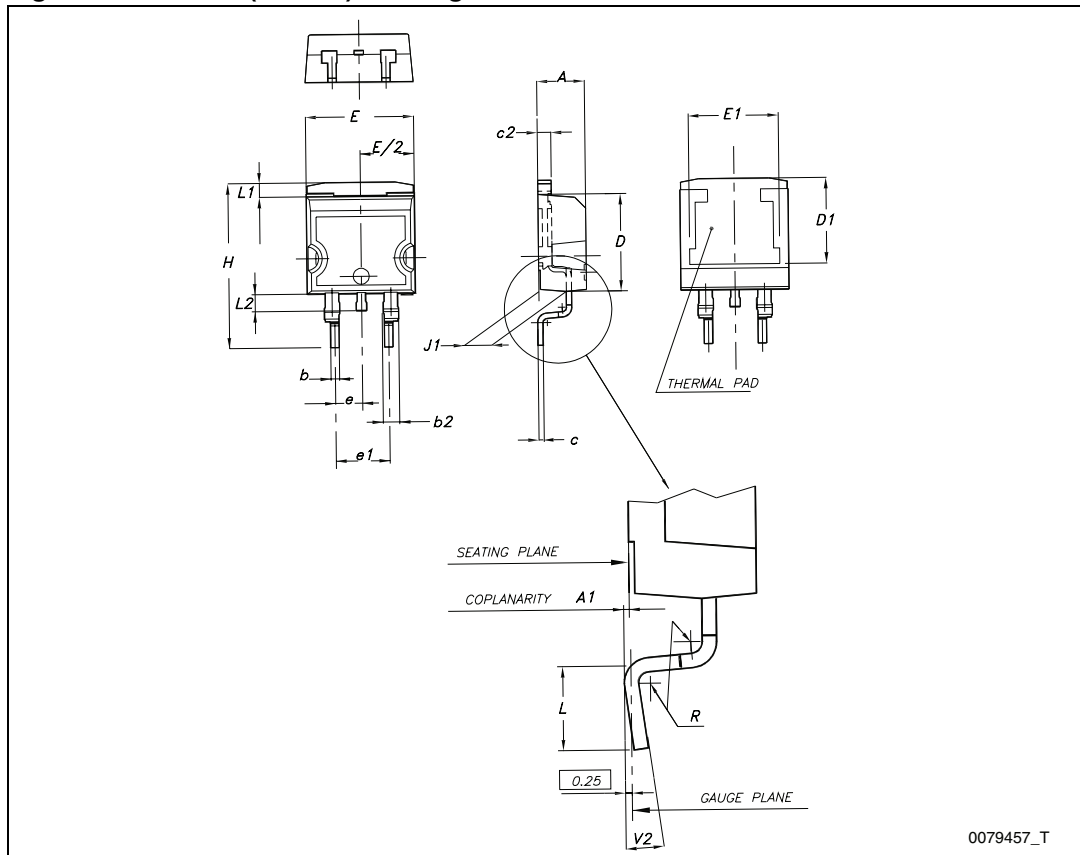
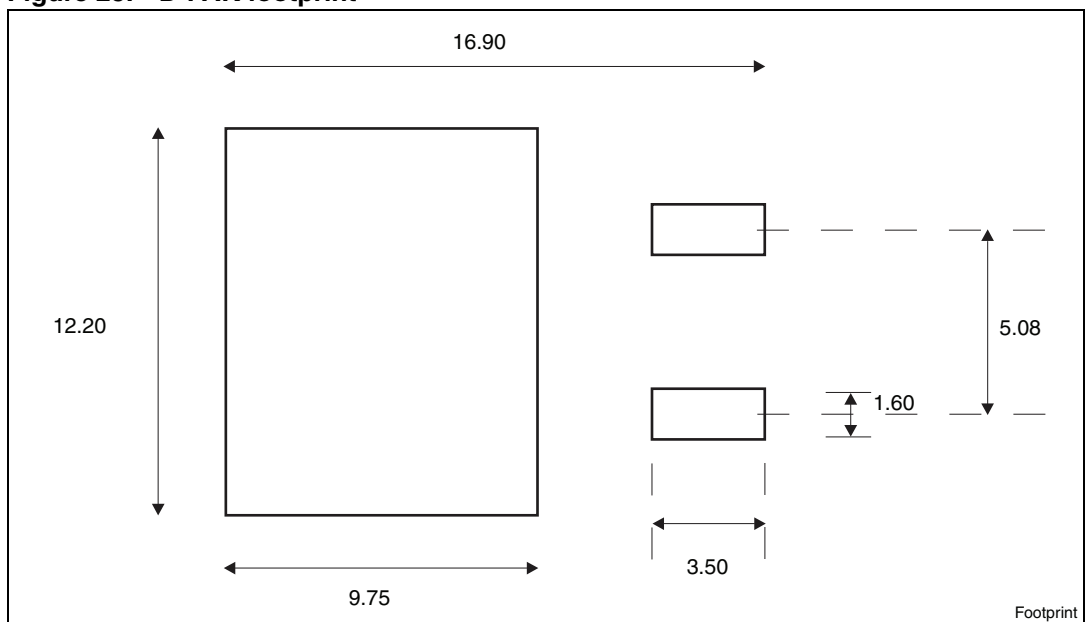
Figure 23. I²PAK (TO-262) drawing

Table 11. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 24. D²PAK (TO-263) drawingFigure 25. D²PAK footprint^(a)

a. All dimensions are in millimeters

Table 12. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 26. TO-220FP drawing

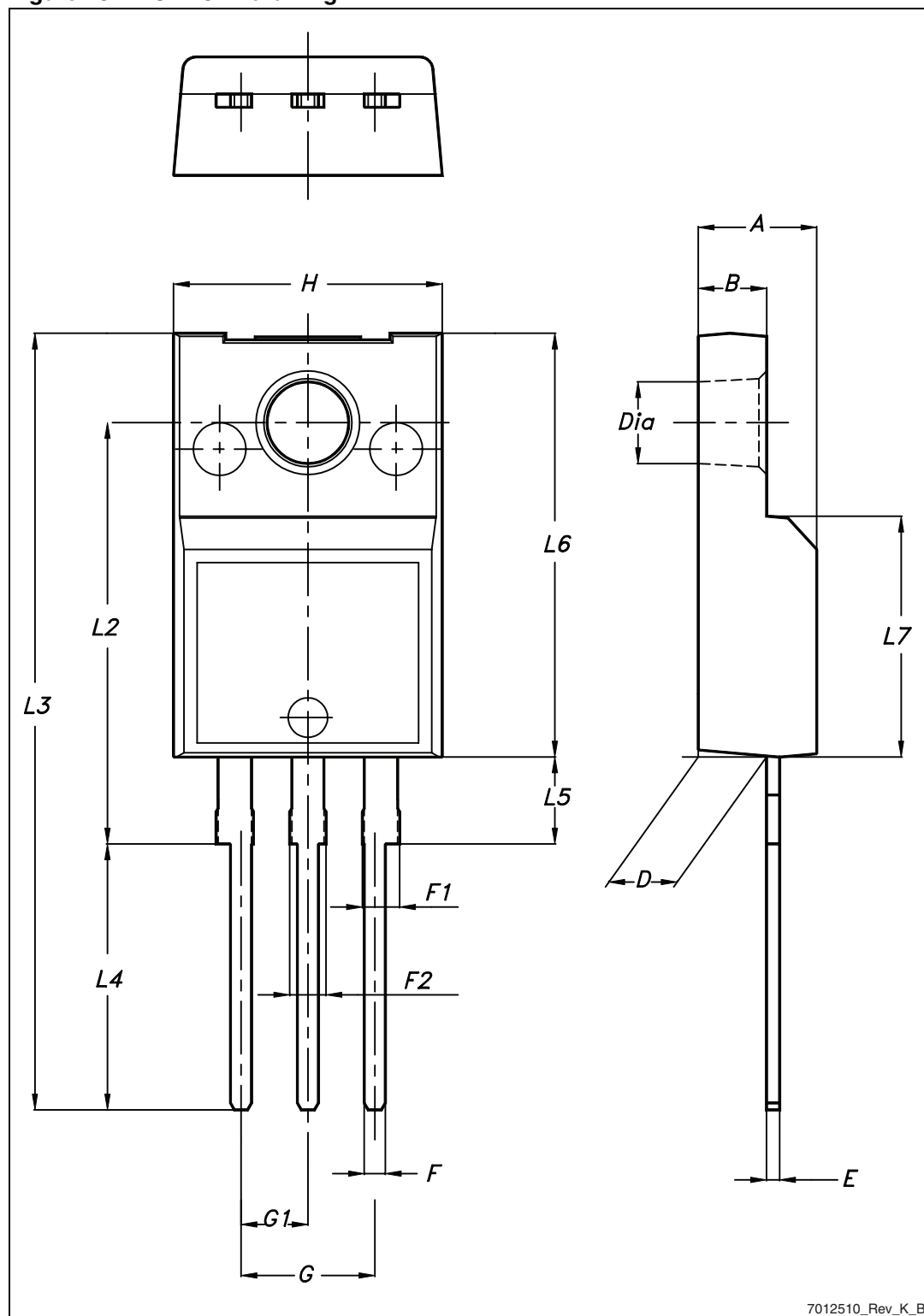
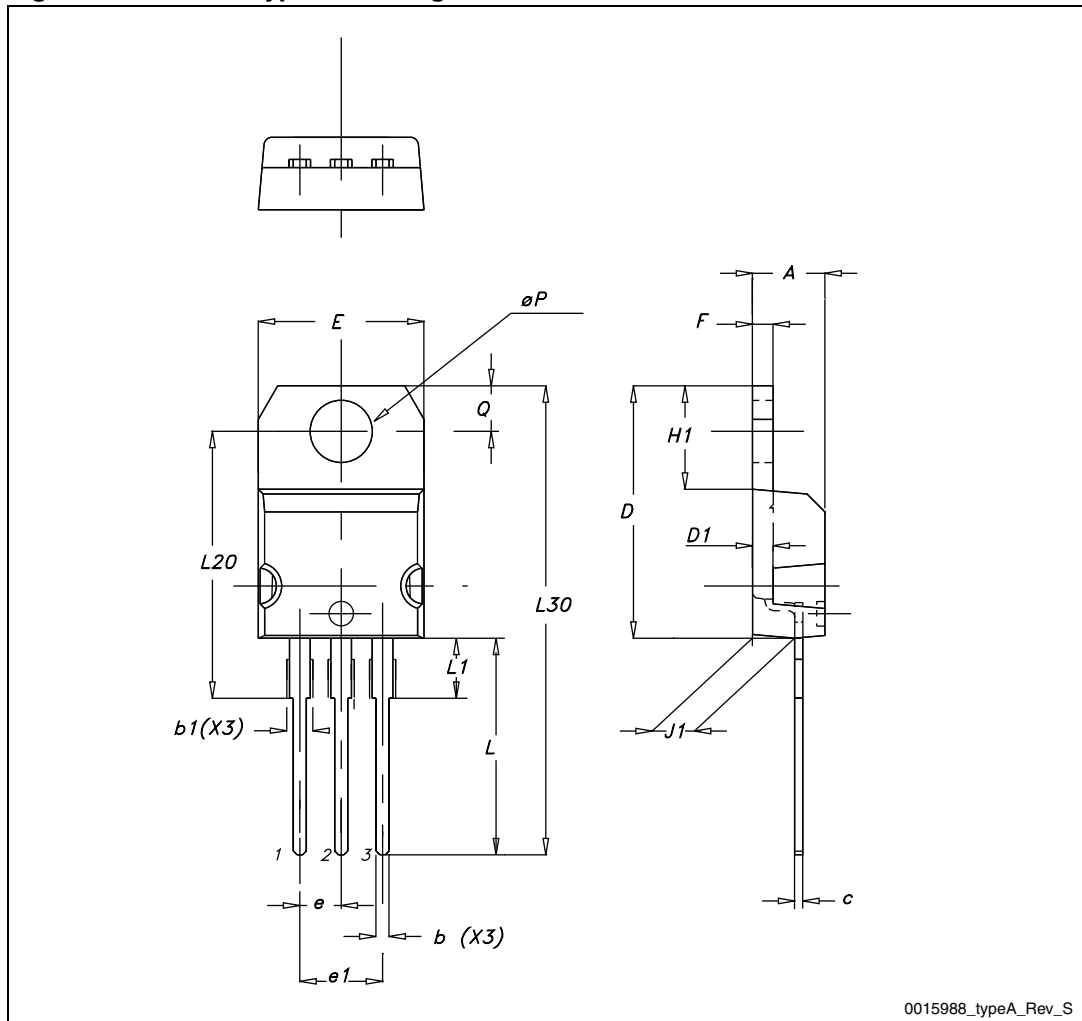


Table 13. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 27. TO-220 type A drawing



5 Packaging mechanical data

Table 14. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 28. Tape

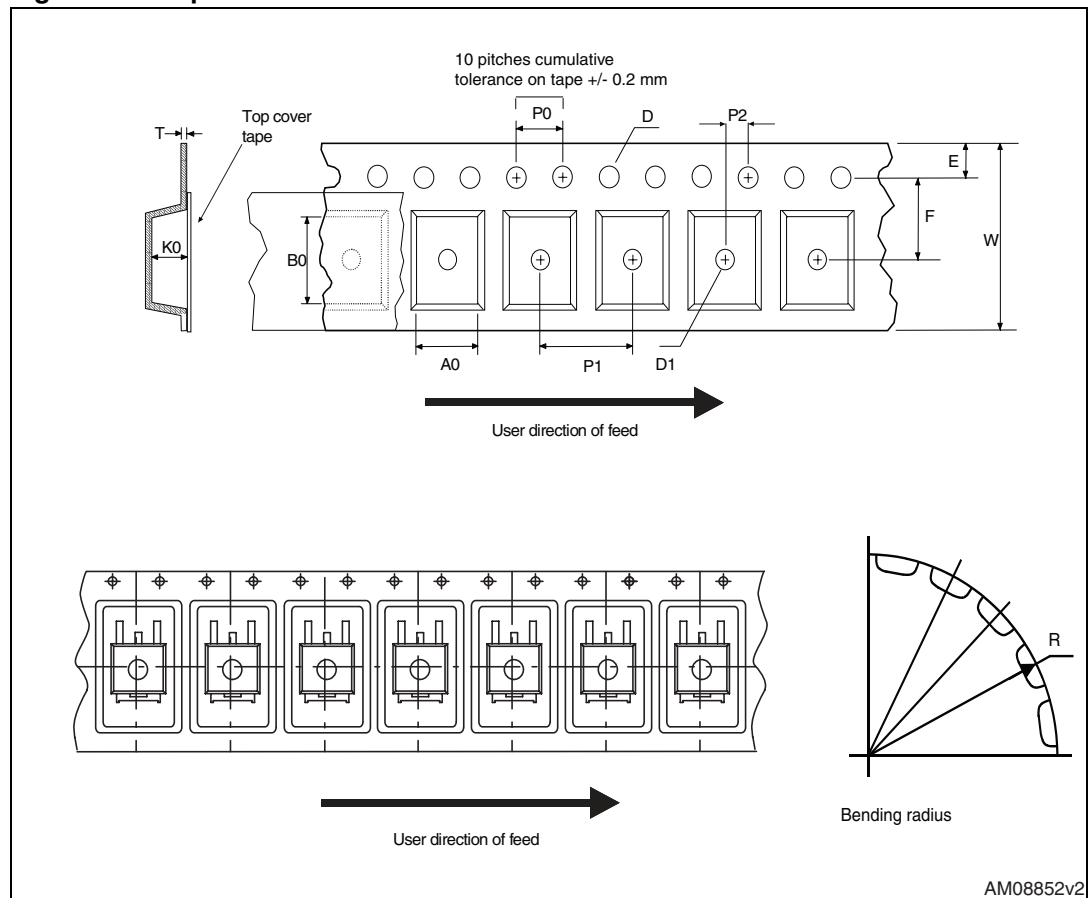
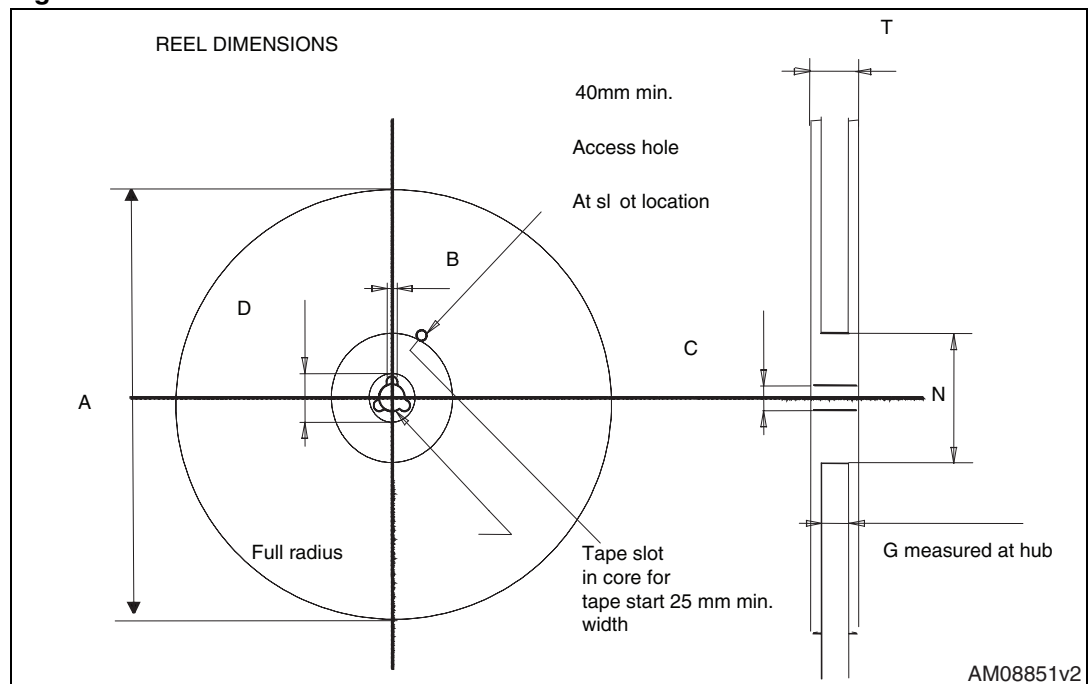


Figure 29. Reel



6 Revision history

Table 15. Document revision history

Date	Revision	Changes
07-Jun-2004	4	Stylesheet update. No content change.
19-Aug-2004	5	Complete version
17-Sep-2004	6	<i>Figure 14</i> has been added
09-Nov-2004	7	Final datasheet
19-Jan-2005	8	Datasheet updated
09-Jun-2005	9	Modified title
27-Jun-2012	10	Inserted commercial type STGB7NC60HD. Minor text changes.

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY TWO AUTHORIZED ST REPRESENTATIVES, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2012 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9